

ABSTRACT OF THE DISCLOSURE

The present invention makes it is possible to provide a manufacturing method of a semiconductor device by which damage by plasma process or doping process during a LDD formation process can be reduced as much as possible. Charge density to be stored in a gate electrode and the damage of an element due to plasma are reduced as much as possible during anisotropic etching of an LDD formation process, by forming an LDD region in the state that a conductive protecting film is formed to cover a whole area of a substrate. Further, damage by charged particles during a process of doping a high concentration of impurity is also reduced.